







RT4823N

Wide Input and Ultra-Low Quiescent Current Boost Converter with High Efficiency

1 General Description

The RT4823N is a boost converter designed to provide a minimum output voltage from a single-cell Li-Ion battery, even when the battery voltage is below the system minimum. The RT4823N allows systems to take advantage of new battery chemistries that can supply significant energy even when the battery voltage is lower than the required voltage for system power ICs. By combining built-in power transistors, synchronous rectification, and low supply current, this IC provides a compact solution for systems using advanced Li-Ion battery chemistries.

In boost mode, output voltage regulation is guaranteed up to a maximum load current of 1500mA. Quiescent current in shutdown mode is less than $1\mu\text{A},$ which maximizes battery life. The regulator transitions smoothly between bypass and normal boost mode. The device can be forced into bypass mode to reduce quiescent current.

The RT4823N is available in the WL-CSP-9B 1.3x1.2 (BSC) package. The recommended junction temperature range is -40° C to 125°C, and the ambient temperature range is -40° C to 85°C.

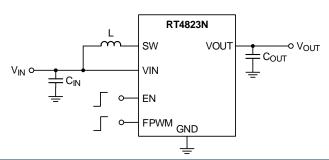
2 Applications

- NFC Device Power Supply
- USB Charging Ports
- PC Accessory Applications
- TWS (True Wireless Stereo) Hall Sensors
- Gaming Device Sensors

3 Features

- Ultra-Low Operating Quiescent Current
- Quick Start-Up Time (< 430μsec)
- Few External Components Needed: A 1μH
 Inductor, A 0402 Case Size Input Capacitor, and A 0603 Case Size Output Capacitor
- Input Voltage Range: 1.8V to 5.5V
- Support VIN > VOUT Operation
- Default Boost Output Voltage Setting: Vout = 5V
- Maximum Continuous Load Current: 1.5A at V_{IN} > 3V Boosting V_{OUT} to 5V
- Up to 93% Efficiency
- EN(H), FPWM(H): Forced PWM Mode
- EN(H): Boost Mode
- EN(L): Shutdown Mode
- Internal Synchronous Rectifier
- Overcurrent Protection
- Cycle-by-Cycle Current Limit
- Overvoltage Protection
- Short-Circuit Protection
- Over-Temperature Protection
- Small WL-CSP-9B 1.3x1.2 (BSC) Package

4 Simplified Application Circuit



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5 Ordering Information

RT4823N □

Package Type⁽¹⁾

WSC: WL-CSP-9B 1.3x1.2 (BSC)

Note 1.

Richtek products are Richtek Green Policy compliant and marked with (1) indicates compatible with the current requirements of IPC/JEDEC J-STD-020.

6 Marking Information



BV: Product Code W: Date Code



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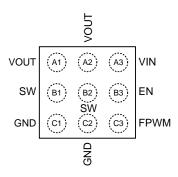
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7 Pin Configuration

(TOP VIEW)



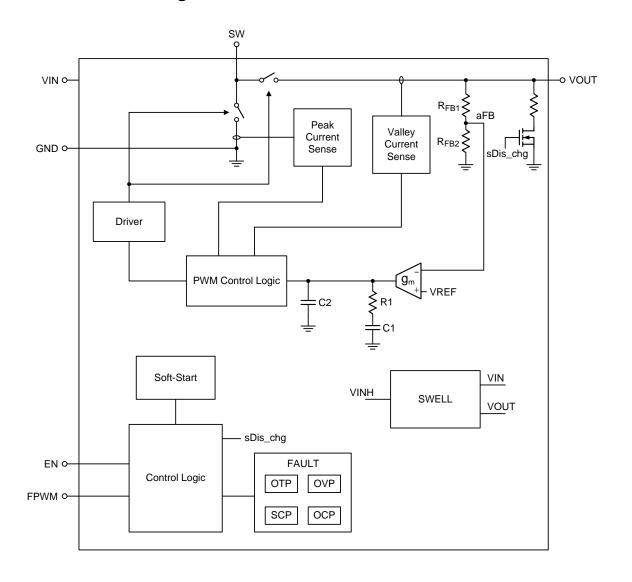
WL-CSP-9B 1.3x1.2 (BSC)

8 Functional Pin Description

Pin No.	Pin Name	Pin Function
A1, A2	VOUT	Output voltage. Place Cout as close as possible to the device.
А3	VIN	Input voltage. This pin must be connected to the input power supply. It is used to provide internal power to the chip.
B1, B2	sw	Switching node. The power inductor should be connected between the SW and the power input.
В3	EN	Enable. When this pin is set to HIGH, the circuit is enabled. Do not leave this pin floating.
C1, C2	GND	Ground. This is the power and signal ground reference for the chip. The Courbypass capacitor should be connected to these pins with the shortest path possible.
C3	FPWM	Force PWM mode. This pin is used to control the converter into forced PWM mode. When this pin is set to HIGH, the circuit enters FPWM mode. Do not leave this pin floating.



9 Functional Block Diagram





10 Absolute Maximum Ratings

(Note 2)

• VIN, VOUT, SW, EN, FPWM	-0.3V to 6.5V
 Power Dissipation, PD @ TA = 25°C 	
• WL-CSP-9B 1.3x1.2 (BSC)	1.54W
Package Thermal Resistance (Note 3)	
• WL-CSP-9B 1.3x1.2 (BSC)	64.9°C/W
• Lead Temperature (Soldering, 10 sec.)	260°C
Junction Temperature	150°C
Storage Temperature Range	−65°C to 150°C
• ESD Susceptibility (Note 4)	

Note 2. Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

HBM (Human Body Model) ----- 2kV

- Note 3. θ_{JA} is simulated under natural convection (still air) at $T_A = 25^{\circ}C$ with the component mounted on a high effective-thermalconductivity four-layer test board on a JEDEC 51-9 thermal measurement standard. θ_{JC} is simulated at the bottom of the package.
- Note 4. Devices are ESD sensitive. Handling precautions are recommended.

11 Recommended Operating Conditions

(Note 5)

Input Voltage Range (Boost Mode)	1.8V to 5.5V
Output Voltage Range	5V
Input Capacitor, CIN	4.7μF
Output Capacitor, COUT	$3.5\mu F$ to $50\mu F$
• Inductance, L	$0.7 \mu H$ to $2.2 \mu H$
Input Current (Average current into SW)	1.8A
Input Current (Peak current into SW)	4A
Ambient Temperature Range	−40°C to 85°C
Junction Temperature Range	-40°C to 125°C

Note 5. The device is not guaranteed to function outside its operating conditions.



12 Electrical Characteristics

 $(V_{IN}=3.6V,~C_{IN}=4.7\mu F,~C_{OUT}=10\mu F,~L1=1\mu H.$ All typical (Typ) limits apply for $T_A=25^{\circ}C$, unless otherwise specified. All minimum (Min) and maximum (Max) apply over the full operating ambient temperature range ($-40^{\circ}C \leq T_A \leq 85^{\circ}C$).

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Input Supply			l.	ı		
VIN Operation Range	VIN		1.8		5.5	V
Into VIN Operating Quiescent Current	IQ_NSW	IOUT = 0mA, VIN = 3.6V, EN = FPWM = GND		0.1	0.5	μА
Into VOUT Standby Mode Quiescent Current	IQ_NSW			2	3	μА
		V _{IN} = 3.6V, V _{OUT} = 5V, FPWM = EN = GND			1	
VIN Quiescent Current (Device Normal Switching)	IQ_sw	VIN = 3.6V, VOUT = 5V, FPWM = GND, EN = VIN		4	6	μΑ
		V _{IN} = 3.6V, V _{OUT} = 5V, FPWM = EN = VIN		10		mA
Power-On Reset	VPOR		1.2	1.5	1.75	V
Enable, FPWM						
Low-Level Input Voltage	VIL				0.4	V
High-Level Input Voltage	ViH		1.2			V
Input Leakage Current	ILK	Input connected to GND or VIN			0.5	μА
Output						
Regulated DC Output Voltage	\/a	1.8V ≤ VIN ≤ 4.8V, IOUT = 0mA, PFM operation	5.04	5.06	5.08	V
Regulated DC Output Voltage	Vout	VIN = 3.6V, IOUT = 1A, PWM operation	4.95	5	5.05	٧
Output Discharge Resistor	RDISCHG	VIN = 3.6V, EN = 0V		100		Ω
Power Switch						
On-Resistance of High-Side MOSFET	RDSON_H			80		mΩ
On-Resistance of Low-Side MOSFET	RDSON_L			80		mΩ
Minimum On-Time	ton_min	VIN = 1.8V to 4.8V, VOUT = 5V	20		60	ns
Maximum Duty Cycle	Dмах	VIN = 1.8V, VOUT = 5V, IL = 400mA	68.8			%
Switch Peak Current Limit (VIN or VOUT > 2.2V)	ILIM_PEAK	VIN = 3.6V, VOUT = 5V		3900		mA
Switch Valley Current Limit (VIN or VOUT > 2.2V)	ILIM_VALLEY	VIN = 3.6V, VOUT = 5V		3600		mA
Negative OCP	ILIM_NEG		-3	-2	-1	Α

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Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit			
Oscillator	Oscillator								
		V _{IN} = 3.6V	3	3.5	4				
Oscillator Frequency	fosc	V _{IN} < 2.5V → start to reduce frequency	2			MHz			
Soft-Start									
Start-Up Time	tstart_bst	V _{IN} = 3.6V, BP = GND, I _{OUT} = 0mA. Time from active EN to VOUT	130	430	550	μs			
Pre-Charge Current Limit	ILIM_PRE	$V_{IN} = 3.6V, EN = 0 \rightarrow 1.8V$	250	300	350	mA			
Protection									
Short-Circuit Protection	VSCP		0.5	0.7	0.9	V			
Over-Temperature Protection	Тотр		140	150	160	°C			
Over-Temperature Protection Hysteresis	Totp_Hys			20		°C			
Overcurrent Protection	locp	VIN = 5V	4	5	5.5	Α			
Efficiency									
		V _{OUT} = 5V, V _{IN} = 3.6V, Load = 10µA		72					
T#C-i		V _{OUT} = 5V, V _{IN} = 3.6V, Load = 10mA		90		0/			
Efficiency	η	V _{OUT} = 5V, V _{IN} = 3.6V, Load = 600mA		93		- %			
		V _{OUT} = 5V, V _{IN} = 3.6V, Load = 1000mA		91					



13 Typical Application Circuit

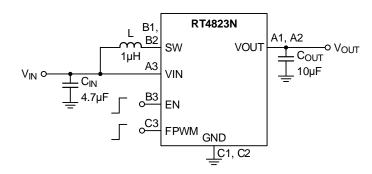
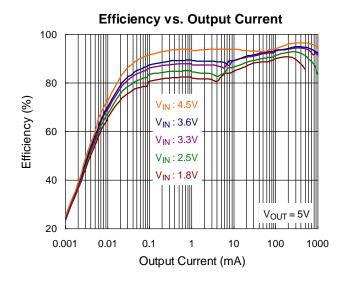


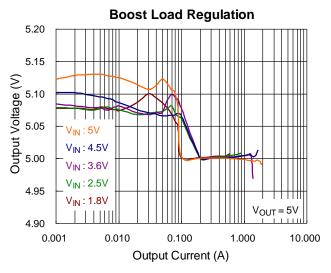
Table 1. Recommended Components Information

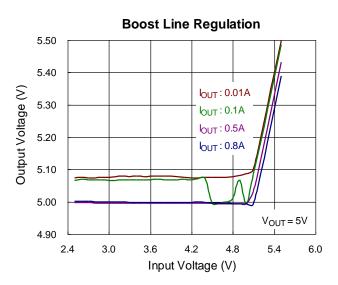
Reference	Part Number	Description	Package	Manufacturer
Cin	GRM155R60J475ME47D	4.7μF/6.3V/X5R	0402	Murata
Соит	GRM188R60J106ME47D	10μF/6.3V/X5R	0603	Murata
L	DFE252012F-1R0M=P2	1.0μH/3.3A	2.5x2.0x1.2mm	Murata

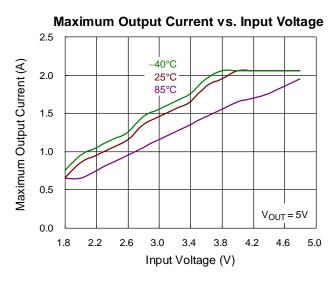


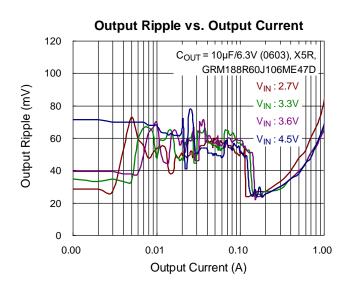
14 Typical Operating Characteristics

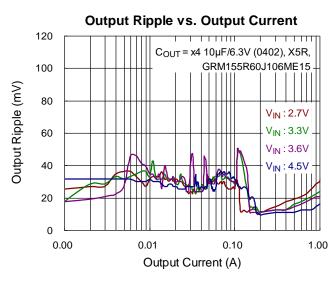




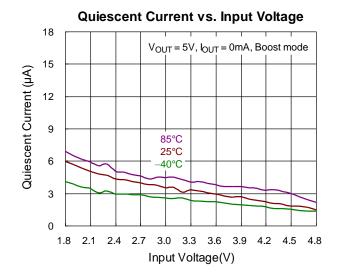


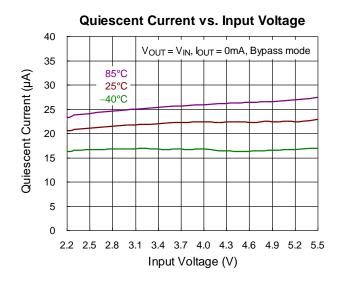


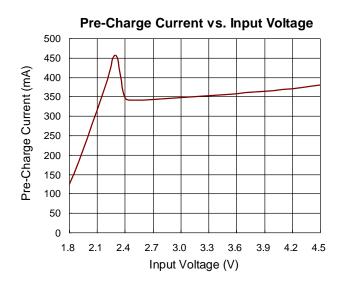


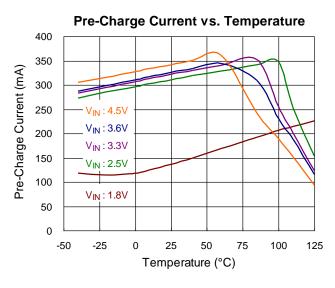


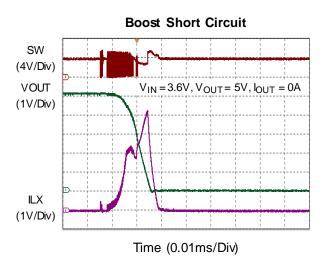


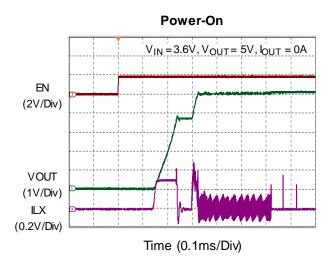








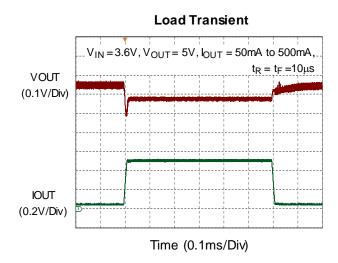


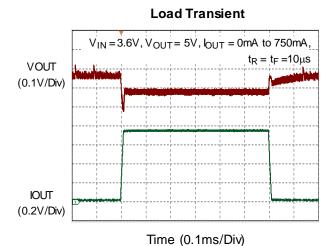


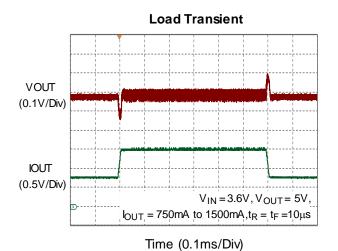
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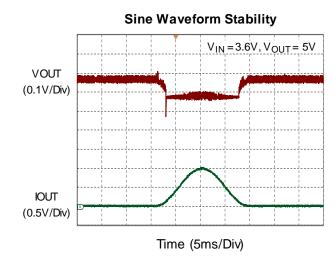
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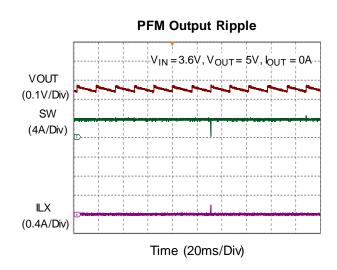


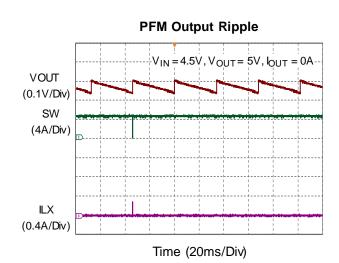


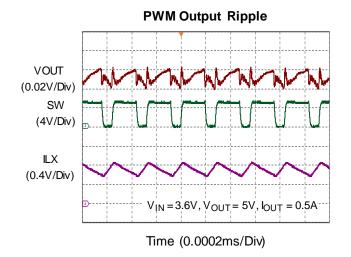


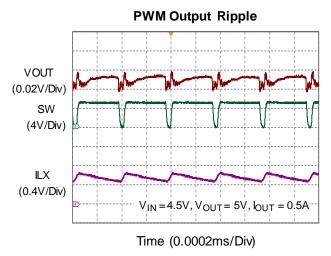














15 Operation

The RT4823N combines built-in power transistors, synchronous rectification, and low supply current, providing a compact solution for systems using advanced Li-Ion battery chemistries.

In boost mode, output voltage regulation is guaranteed up to a maximum load current of 1.5A. Quiescent current in shutdown mode is less than 1µA, which maximizes battery life.

15.1 Power-On Reset

If the input voltage is lower than the POR threshold, the internal digital and analog circuits are disabled. If the input voltage is higher than the POR threshold, the boost converter behaves as follows:

- 1. The IC digital circuit is activated.
- 2. After the EN pin is turned on, internal registers start to load the default value via eFuse.
- 3. The boost converter enters free-running mode (details in the free-running mode section).
- 4. If VOUT > 2.2V (or VIN > 2.2V), the boost converter will enter closed-loop control.

Figure 1 and Figure 2 show the eFuse download diagram and flow chart. When the input voltage is higher than the POR threshold and EN goes high, eFuse starts to load in the digital circuit. The deglitch time is 3µs to 15µs (maximum), and the eFuse download time is 16µs to 24µs (maximum). When eFuse data starts to download, the RT4823N internal circuit ensure the download progress is completed unless VIN < POR threshold.

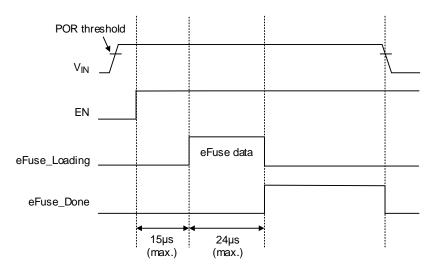


Figure 1. eFuse Download Timing Diagram

15.2 Free-Running Mode

If both VIN and VOUT are lower than 2.2V, the boost converter will enter free-running mode. In this mode, the switching frequency is 1.5MHz and the duty cycle of the boost converter is 25%. This is the power-on stage, and a current limit function is implemented for converter soft-start. The current limit level should be lower than 900mA.

EN and FPWM 15.3

As shown in Table 2, there are three device states in the RT4823N. When both EN and FPWM are pulled low, the device enters shutdown mode and the quiescent current is less than 1µA. If EN is pulled high, the RT4823N enters boost mode with low quiescent operation. When the RT4823N is in boost mode and FPWM is pulled high, the RT4823N enters FPWM mode. There should be a delay time (< 250μs) from when EN is pulled high to when power is ready to guarantee normal operation.



Table 2. Pin Configuration for Converter

EN Input	FPWM Input	Mode Define	Device State
0 Shutdown mode The device is shut down. The device shutdown approximately about 1μA (maximum).		The device is shut down. The device shutdown current is approximately about $1\mu A$ (maximum).	
		The device is active in Boost PFM low quiescent mode. The supply current is approximately 4µA (typical).	
1	1	Boost PWM	The device is in force PWM mode.

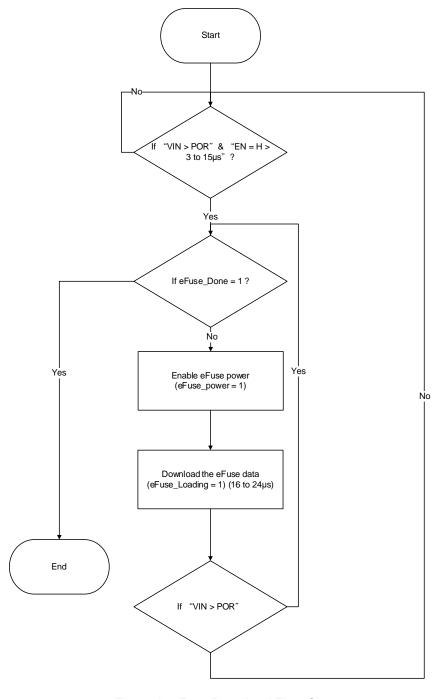


Figure 2. eFuse Download Flow Chart

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15.4 Enable

The boost converter can be enabled or disabled using the EN pin. When the EN pin voltage is higher than the logic-high threshold, the device starts operating according to the operation diagram shown in <u>Figure 2</u>. In shutdown mode, the converter stops switching, and the internal control circuit is turned off. The output voltage discharges through component consumption (e.g., capacitor ESR), as there is no dedicated discharge function in this state.

15.5 Soft-Start State

During the soft-start state, if VOUT reaches 99% of Vout_Target. The RT4823N will enter boost operation. When the system powers on with heavy loading (higher than pre-charge current), the RT4823N remains in the pre-charge state until the load is released.

15.6 Boost/Auto Bypass Mode

There are two normal operation modes: boost mode and auto bypass mode. In boost mode ($VIN - 0.3V < VOUT_Target$), the converter boosts the output voltage to $VOUT_Target$, delivering power to the load through internal synchronous switches after the soft-start state. In auto bypass mode ($VIN - 0.3V \ge VOUT_Target$), the input voltage is delivered directly to the output terminal, providing maximum current capacity with the RT4823N. Detailed information is shown below.

15.7 Boost Mode (Auto PFM/PWM Control Method)

To save power and improve efficiency at low loads, the boost converter operates in PFM (Pulse Frequency Modulation) as the inductor drops into DCM (Discontinuous Current Mode). The switching frequency is proportional to the load to maintain output voltage regulation. When the load increases and the inductor current enters continuous current mode, the boost converter automatically switches to PWM mode.

Table 3. The RT4823N Start-Up Description

Mode	Description	Condition					
LIN	Linear startup	V _{IN} - 200mV ≥ V _{OUT}					
Soft-Start	Boost soft-start	0.99 x VouT_Target > VouT ≥ ViN - 200mV					
Boost	Boost mode	V _{OUT_Target} ≥ 0.99 x V _{OUT_Target}					
	If VIN increases higher than VOUT						
Auto Bypass	Auto bypass mode	V _{IN} ≥ V _{OUT} Control loop auto transfer between auto bypass mode and boost mode.					

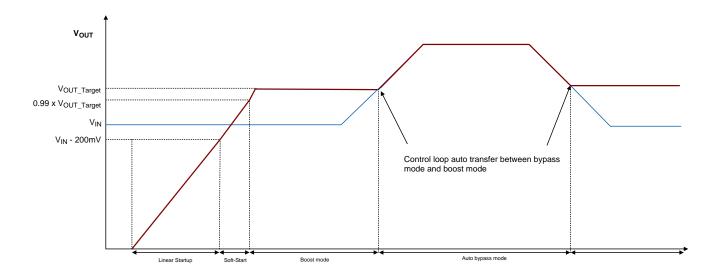


Figure 3. V_{OUT} Mode Transition Diagram with EN L to H and V_{IN} Variation ($I_{OUT} = 0A$)

15.8 **Protection**

The RT4823N features several protections, which are listed in the table below. The table describes the protection behaviors.

Protection Type	Fault Event Trigger	Fault Deglitch Time	Protection Method	Fault Protection Latch Time	Reset Method
OCP_IL5A	IL_peak > 5A	No delay	Turn off UG, LG	20ms, Auto-recovery	IL_peak < 5A
OCP	IL_peak > 3.6A	No delay	Stop LG switching	N/A	IL_valley < 3.3A
OVP	Vout > 6V	100ns	Turn off UG, LG	N/A	V _{OUT} < 6V
SCP	V _{OUT} < 0.7V	No delay	Turn off UG, LG	20ms, Auto-recovery	V _{OUT} > 0.7V
OTP	TEMP > 150°C	170μs	Turn off UG, LG	Turn off UG, LG	TEMP < 130°C
SCP_SS	VIN - VOUT > 0.2V	2ms	UG OCP = 0.3A	N/A	VIN - VOUT < 0.2V



16 Application Information

(Note 6)

16.1 Start-Up

The RT4823N can be powered via the EN pin. The following steps must be followed for startup.

- 1. Configure the input voltage (VIN) within the recommended operating range.
- Set the MODE pin for PFM or PWM mode selection.
- Enable the boost converter using the EN pin.

16.2 Power-Off

When the RT4823N is turned off, the device enters a shutdown state. In this mode, the converter stops its switching operation, the internal control circuitry is deactivated, and the load is disconnected from the input. As a result, the output voltage may decrease below the input voltage while in shutdown. The RT4823N incorporates a discharge function, causing the output voltage to drop rapidly when the device is powered off.

Power Frequency Modulation (PFM) 16.3

PFM is used to improve efficiency at light load. When the output voltage is lower than a set threshold voltage, the converter will operate in PFM. It raises the output voltage with several pulses until the loop exits PFM.

Over-Temperature Protection (OTP)

The device has a built-in temperature sensor which monitors the internal junction temperature. If the temperature exceeds the threshold, the device stops operating. As soon as the IC temperature decreases below the threshold with a hysteresis, it starts operating again. The built-in hysteresis is designed to avoid unstable operation at IC temperatures near the over-temperature threshold.

16.5 **Inductor Selection**

The primary concern in inductor selection is the maximum load of the application. An example is given by the application conditions and equations below.

Application conditions:

VIN = 3V, VOUT = 5V, IOUT = 1.5A, converter efficiency = 81%, Frequency = 3.5MHz, L = 1 μ H.

Step 1: To calculate the input current (IIN).

$$I_{IN} = \frac{V_{OUT} \times I_{OUT}}{V_{IN} \times Eff} = 3.086A$$

Step 2: To calculate the duty cycle of the boost converter.

$$D=1-\frac{V_{IN}}{V_{OUT}}=0.4$$

Step 3: To calculate the peak current of the inductor.

$$I_{L(Peak)} = I_{IN} + 0.5 \times \frac{V_{IN} \times D}{L \times Freq} = 3.258A$$

The recommended nominal inductance value is 1µH. It is recommended to use an inductor with a DC saturation current of at least 3300mA.



16.6 Input Capacitor Selection

It is recommended to use an input capacitor with a minimum capacitance of $4.7\mu F$ and a rate voltage of 6.3V for DC bias. This helps to improve the transient response of the regulator and the EMI performance of the entire power supply circuit for the switch (SW). Additionally, the input capacitor should be placed as close as possible to the VIN and GND pins of the IC.

16.7 Output Capacitor Selection

It is recommended to use at least a $10\mu\text{F}$ capacitor to reduce VouT ripple. The output voltage ripple is inversely proportional to the output capacitance (Cout). The output capacitor should be selected based on the desired output ripple, which can be calculated using the following formula:

$$V_{RIPPLE(P-P)} = t_{ON} \times \frac{I_{LOAD}}{C_{OUT}}$$

and

$$t_{ON} = t_{SW} \times D = t_{SW} \times \left(1 - \frac{V_{IN}}{V_{OUT}}\right)$$

therefore:

$$C_{OUT} = t_{SW} \times \left(1 - \frac{V_{IN}}{V_{OUT}}\right) \times \frac{I_{LOAD}}{V_{RIPPLE(P-P)}}$$

and

$$t_{SW} = \frac{1}{f_{SW}}$$

The maximum VRIPPLE occurs at minimum input voltage and maximum output load.

16.8 Boost Converter Sleeping Mode Operation

The RT4823N implements both PFM (Pulse Frequency Modulation) mode and PWM (Pulse Width Modulation) mode. The PFM mode is designed for power-saving operation when the system operates under light load conditions.

There is a mode transition between PFM and PWM modes. When the system load increases, the operating mode transitions from PFM to PWM. Please note that within this small load current range, the mode change can cause an increase in output ripple.

16.9 Current Limit

The RT4823N employs a valley-current limit detection scheme to sense the inductor current during the off-time. When the load current increases such that it exceeds the valley current-limit threshold, the off-time is extended until the current decreases to the valley-current threshold. The next on-time begins after the current decreases to the valley-current threshold. The on-time is determined by the ratio of (Vout – VIN) / Vout. The output voltage decreases when the load current further increases. The current limit function is implemented using this scheme. Refer to Figure 4 for more details.

16.10 Overcurrent Protection (OCP)

The RT4823N implements an OCP function. When the converter operates in boost mode, the peak current limit and valley current limit functions cannot protect the IC from short circuits or extremely high loads. Therefore, the RT4823N includes a truth disconnection function. When the peak current exceeds 5A (typical), the boost converter will turn off both the high-side MOSFET (UG) and the low-side MOSFET (LG).

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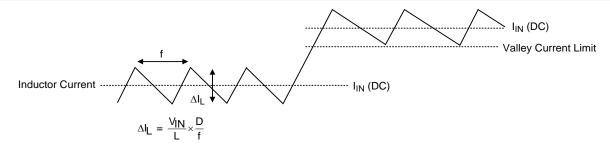


Figure 4. Inductor Currents in Current Limit Operation

16.11 Thermal Considerations

The junction temperature should never exceed the absolute maximum junction temperature TJ(MAX), listed under Absolute Maximum Ratings, to avoid permanent damage to the device. The maximum allowable power dissipation depends on the thermal resistance of the IC package, the PCB layout, the rate of surrounding airflow, and the difference between the junction and ambient temperatures. The maximum power dissipation can be calculated using the following formula:

 $PD(MAX) = (TJ(MAX) - TA) / \theta JA$

where TJ(MAX) is the maximum junction temperature, TA is the ambient temperature, and θ JA is the junction-toambient thermal resistance.

For continuous operation, the maximum operating junction temperature indicated under Recommended Operating Conditions is 125°C. The junction-to-ambient thermal resistance, θ_{JA} , is highly package dependent. For a WL-CSP-9B 1.3x1.2 (BSC) package, the thermal resistance, 0JA, is 64.9°C/W on a standard JEDEC 51-9 high effectivethermal-conductivity four-layer test board. The maximum power dissipation at TA = 25°C can be calculated as below:

 $PD(MAX) = (125^{\circ}C - 25^{\circ}C) / (64.9^{\circ}C/W) = 1.54W$ for a WL-CSP-9B 1.3x1.2 (BSC) package.

The maximum power dissipation depends on the operating ambient temperature for the fixed TJ(MAX) and the thermal resistance, θ_{JA} . The derating curve in Figure 5 allows the designer to see the effect of rising ambient temperature on the maximum power dissipation.

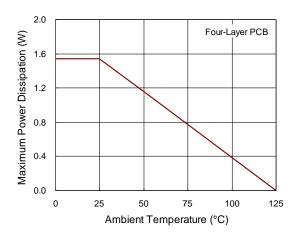


Figure 5. Derating Curve of Maximum Power Dissipation

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16.12 Layout Considerations

The PCB layout is an important step to maintain the high performance of the RT4823N.

Both the high current and the fast switching nodes demand full attention in the PCB layout to save the robustness of the RT4823N. Improper layout might show the symptoms of poor line or load regulation, ground and output voltage shifts, stability issues, unsatisfying EMI behavior or worsened efficiency. For the best performance of the RT4823N, the following PCB layout guidelines must be strictly followed.

- Place the input and output capacitors as close as possible to the input and output pins, respectively, for effective filtering.
- For thermal considerations, it is necessary to maximize the copper area for the power stage area, especially around the SW pin.

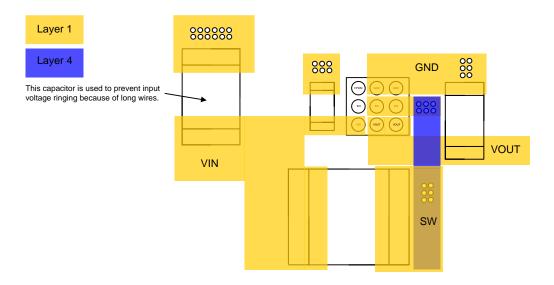


Figure 6. PCB Layout Guide

Note 6. The information provided in this section is for reference only. The customer is solely responsible for designing, validating, and testing any applications incorporating Richtek's product(s). The customer is also responsible for applicable standards and any safety, security, or other requirements.

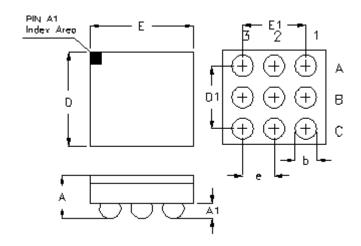
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17 Outline Dimension

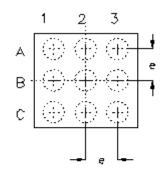


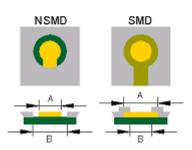
Symbol	Dimensions I	In Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.500	0.600	0.020	0.024	
A1	0.170	0.230	0.007	0.009	
b	0.240	0.300	0.009	0.012	
D	1.160	1.240	0.046	0.049	
D1	0.8	300	0.0	031	
E	1.260	1.340	0.050	0.053	
E1	0.800		0.031		
е	0.4	100	0.0)16	

9B WL-CSP 1.3x1.2 Package (BSC)



18 Footprint Information



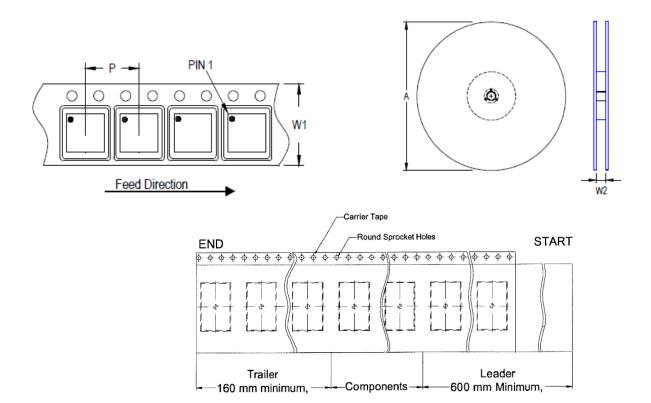


Pookogo	Number of		Footpri	Tolerance			
Package	Pin	Type	е	Α	В	Tolerance	
WL CCD4 2v4 2 0/DCC)	CSD4 3×4 3 0/BSC) 0		0.400	0.240	0.340	.0.025	
WL-CSP1.3x1.2-9(BSC)	9	SMD	0.400	0.270	0.240	±0.025	

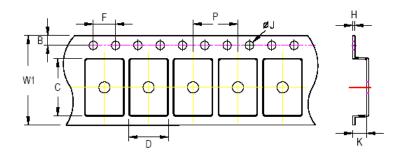


19 Packing Information

19.1 Tape and Reel Data



Package Type	Tape Size (W1) (mm)	Pocket Pitch (P) (mm)	Reel Si	ze (A)	Units per Reel	Trailer (mm)	Leader (mm)	Reel Width (W2) Min/Max (mm)
WL-CSP 1.3x1.2	8	4	180	7	3,000	160	600	8.4/9.9



C, D, and K are determined by component size.

The clearance between the components and the cavity is as follows:

- For 8mm carrier tape: 0.5mm max.

Tana Siza	W1	Р		В		F		Ø٦		K		Н
Tape Size	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Max
8mm	8.3mm	3.9mm	4.1mm	1.65mm	1.85mm	3.9mm	4.1mm	1.5mm	1.6mm	0.7mm	0.8mm	0.6mm



19.2 Tape and Reel Packing

Step	Photo/Description	Step	Photo/Description
1	Reel 7"	4	12 inner boxes per outer box
2	Packing by Anti-Static Bag	5	Outer box Carton A
3	3 reels per inner box Box A	6	

Container	R	eel	Вох			Carton			
Package	Size	Units	Item	Reels	Units	Item	Boxes	Unit	
WL-CSP	7"	2 000	Box A	3	9,000	Carton A	12	108,000	
1.3x1.2	1	3,000	Box E	1	3,000	For C	combined or Partial	Reel.	

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19.3 **Packing Material Anti-ESD Property**

Surface Resistance	Aluminum Bag	Reel	Cover tape	Carrier tape	Tube	Protection Band
Ω /cm ²	10 ⁴ to 10 ¹¹					

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20 Datasheet Revision History

Version	Date	Description	Item
00	2023/2/15	Final	Marking Information on P2 Operation on P4, 5
01	2024/11/12	Modify	General Description on page 1 - Added the description of temperature Ordering Information on page 2 - Added note Electrical Characteristics on page 7 - Modified symbol Application Information on page 21 - Updated declaration Packing Information on page 24, 25 - Updated packing information

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